

12 53. (Amended) A method of producing a programmable conductor memory device, said method comprising;

forming first and second digit lines;

forming first and second programmable conductor memory elements arranged to store complementary logic states;

forming first and second access transistors for respectively coupling said first and second memory elements to said first and second digit lines;

forming a precharge circuit for precharging said first and second digit lines to a first voltage;

forming respective row lines for operating said access transistors to couple said memory elements to respective digit lines; and

forming a sense amplifier which has inputs respectively coupled to said digit lines.

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Please add the following new claim.

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13 59. (Newly Added) A method of producing a programmable conductor memory device, said method comprising;

forming first and second digit lines;

forming first and second programmable conductor memory elements arranged to store complementary logic states;

forming first and second access transistors for respectively coupling said first and second memory elements to said first and second digit lines;

A3 forming a precharge circuit for precharging said first and second digit lines to a first voltage;

forming a circuit for operating said access transistors to couple said memory elements to respective digit lines; and

forming a sense amplifier which has inputs respectively coupled to said digit lines.

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